

isc Silicon NPN Power Transistor

BUJ303A

DESCRIPTION

- High Voltage
- · High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

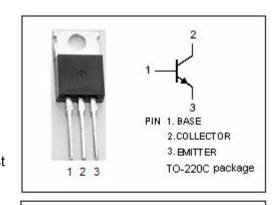
 Designed for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

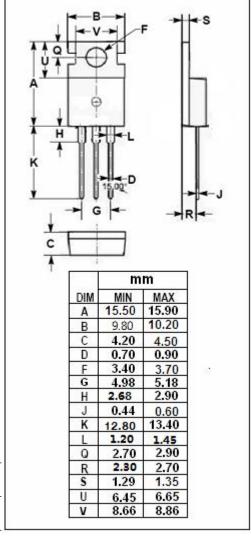
ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	1000	V
V _{CEO}	Collector-Emitter Voltage	500	V
V _{EBO}	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	5	Α
I _{CM}	Collector Current-Peak	10	Α
I _B	Base Current	2	Α
I _{BM}	Base Current-Peak	4	Α
Pc	Collector Power Dissipation @T _C =25°C	120	W
T _j	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature Range	-65~150	$^{\circ}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	1.04	K/W







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

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PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
Collector-Emitter Sustaining Voltage	I _C =50mA; I _B = 0	500			٧
Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 0.6A			1.5	V
Base-Emitter Saturation Voltage	I _C = 3A; I _B = 0.6A			1.3	V
Collector Cutoff Current	V _{CB} =1000V ;V _{BE} = 0 V _{CB} =1000V ;V _{BE} = 0;T _C =125°C			1 2	mA
Emitter Cutoff Current	V _{EB} = 9V; I _C = 0			0.1	mA
Base Cutoff Current	V _{CE} = 500V; I _C = 0			0.1	mA
DC Current Gain	I _C = 5mA; V _{CE} = 5V	10		35	
DC Current Gain	I _C = 0.5A; V _{CE} = 5V	14		35	
	Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage Collector Cutoff Current Emitter Cutoff Current Base Cutoff Current DC Current Gain	Collector-Emitter Saturation Voltage I_{C} = 3A; I_{B} = 0.6A Base-Emitter Saturation Voltage I_{C} = 3A; I_{B} = 0.6A Collector Cutoff Current V_{CB} =1000V; V_{BE} = 0 V_{CB} =1000V; V_{BE} = 0; V_{CE} =1000V; V_{CE} = 0; V_{CE} = 9V; V_{CE} = 0 DC Current Gain V_{CE} = 5MA; V_{CE} = 5V	Collector-Emitter Saturation Voltage $I_C=3A;\ I_B=0.6A$ Base-Emitter Saturation Voltage $I_C=3A;\ I_B=0.6A$ Collector Cutoff Current $V_{CB}=1000V;V_{BE}=0$ $V_{CB}=1000V;V_{BE}=0;T_{C}=125^{\circ}C$ Emitter Cutoff Current $V_{CE}=9V;\ I_C=0$ Base Cutoff Current $V_{CE}=500V;\ I_C=0$ DC Current Gain $I_C=5mA;\ V_{CE}=5V$ 10	Collector-Emitter Saturation Voltage $I_{C}=3A;\ I_{B}=0.6A$ Base-Emitter Saturation Voltage $I_{C}=3A;\ I_{B}=0.6A$ Collector Cutoff Current $V_{CB}=1000V;V_{BE}=0$ $V_{CB}=1000V;V_{BE}=0;T_{C}=125^{\circ}C$ Emitter Cutoff Current $V_{EB}=9V;\ I_{C}=0$ Base Cutoff Current $V_{CE}=500V;\ I_{C}=0$ DC Current Gain $I_{C}=5mA;\ V_{CE}=5V$ 10	Collector-Emitter Saturation Voltage $I_C = 3A$; $I_B = 0.6A$ 1.5 Base-Emitter Saturation Voltage $I_C = 3A$; $I_B = 0.6A$ 1.3 Collector Cutoff Current $V_{CB} = 1000V$; $V_{BE} = 0$ 1 Emitter Cutoff Current $V_{CB} = 9V$; $I_C = 0$ 0.1 Base Cutoff Current $V_{CE} = 500V$; $I_C = 0$ 0.1 DC Current Gain $I_C = 5mA$; $V_{CE} = 5V$ 10 35



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